

ABSTRACT

The image capture period of an imaging cell, or the total time that an imaging cell is exposed to light energy, is substantially increased by  
5 utilizing a non-volatile memory (NVM), such as an electrically-erasable, programmable, read-only-memory (EEPROM) structure. The NVM structure stores and integrates charges that are proportional to the absorbed photons over a large number of sequential integration periods.

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